

Dun-Jun Chen

List of Publications by Year in Descending Order

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The third column is the impact factor (IF) of the journal, and the fourth column is the number of citations of the article.

106
papers

1,189
citations

19
h-index

30
g-index

116
ext. papers

1,537
ext. citations

4.2
avg, IF

4.35
L-index

| # | Paper | IF | Citations |
|-----|---|------|-----------|
| 106 | 1.2 kV/25 A Normally off P-N Junction/AlGaIn/GaN HEMTs With Nanosecond Switching Characteristics and Robust Overvoltage Capability. <i>IEEE Transactions on Power Electronics</i> , 2022 , 37, 26-30 ² | 3.7 | 3 |
| 105 | The Sensing Mechanism of InAlN/GaN HEMT. <i>Crystals</i> , 2022 , 12, 401 | 2.3 | 1 |
| 104 | 3-D Simulation Study of a Normally-OFF GaN Lateral Multi-Channel JFET With Optimized Electrical Field Transfer Terminal Structure. <i>IEEE Transactions on Electron Devices</i> , 2022 , 69, 1918-1923 | 2.9 | |
| 103 | Normally-off GaN HEMTs with InGaN p-gate cap layer formed by polarization doping. <i>Applied Physics Express</i> , 2022 , 15, 016502 | 2.4 | 2 |
| 102 | 4H-SiC B-i-p extreme ultraviolet detector with gradient doping-induced surface junction. <i>IEEE Electron Device Letters</i> , 2022 , 1-1 | 4.4 | 0 |
| 101 | 1000-W Resistive Energy Dissipating Capability Against Inductive Transients Demonstrated in Non-Avalanche AlGaIn/GaN Schottky Diode. <i>IEEE Electron Device Letters</i> , 2021 , 42, 1743-1746 | 4.4 | 0 |
| 100 | Over 1200 V Normally-OFF p-NiO gated AlGaIn/GaN HEMTs on Si with a Small Threshold Voltage Shift. <i>IEEE Electron Device Letters</i> , 2021 , 1-1 | 4.4 | 2 |
| 99 | NiO/AlGaIn interface reconstruction and transport manipulation of p-NiO gated AlGaIn/GaN HEMTs. <i>Applied Physics Reviews</i> , 2021 , 8, 041405 | 17.3 | 2 |
| 98 | Low-Voltage p-i-n GaN-Based Alpha-Particle Detector With High Energy Resolution. <i>IEEE Electron Device Letters</i> , 2021 , 1-1 | 4.4 | 1 |
| 97 | High sensitivity x-ray detectors based on 4H-SiC p-i-n structure with 80 nm thick intrinsic layer. <i>Journal of Vacuum Science and Technology B: Nanotechnology and Microelectronics</i> , 2021 , 39, 022202 | 1.3 | 1 |
| 96 | Investigations of Sidewall Passivation Technology on the Optical Performance for Smaller Size GaN-Based Micro-LEDs. <i>Crystals</i> , 2021 , 11, 403 | 2.3 | 4 |
| 95 | Enhanced Stability and Sensitivity of AlGaIn/GaN-HEMTs pH Sensor by Reference Device. <i>IEEE Sensors Journal</i> , 2021 , 21, 9771-9776 | 4 | 2 |
| 94 | Highly solar-blind ultraviolet selective metal-semiconductor-metal photodetector based on back-illuminated AlGaIn heterostructure with integrated photonic crystal filter. <i>Applied Physics Letters</i> , 2021 , 118, 142105 | 3.4 | 5 |
| 93 | Progress on AlGaIn-based solar-blind ultraviolet photodetectors and focal plane arrays. <i>Light: Science and Applications</i> , 2021 , 10, 94 | 16.7 | 51 |
| 92 | High Performance Quasi-Vertical GaN Junction Barrier Schottky Diode with Zero Reverse Recovery and Rugged Avalanche Capability 2021 , | | 4 |
| 91 | A High Quantum Efficiency Narrow-Band UV-B AlGaIn p-i-n Photodiode With Polarization Assistance. <i>IEEE Photonics Journal</i> , 2021 , 13, 1-8 | 1.8 | 1 |
| 90 | An improved design for e-mode AlGaIn/GaN HEMT with gate stack B _{0.5} Ga ₂ O ₃ /p-GaN structure. <i>Journal of Applied Physics</i> , 2021 , 130, 035703 | 2.5 | 2 |

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|----|---|-----|----|
| 89 | High-Voltage Quasi-Vertical GaN Junction Barrier Schottky Diode With Fast Switching Characteristics. <i>IEEE Electron Device Letters</i> , 2021 , 42, 974-977 | 4.4 | 13 |
| 88 | 3.4-kV AlGaIn/GaN Schottky Barrier Diode on Silicon Substrate With Engineered Anode Structure. <i>IEEE Electron Device Letters</i> , 2021 , 42, 208-211 | 4.4 | 8 |
| 87 | High-performance normally off p-GaN gate high-electron-mobility transistor with In _{0.17} Al _{0.83} N barrier layer design. <i>Optical and Quantum Electronics</i> , 2021 , 53, 1 | 2.4 | 3 |
| 86 | High Performance Wide Angle DBR Design for Optoelectronic Devices. <i>IEEE Photonics Journal</i> , 2021 , 13, 1-6 | 1.8 | 2 |
| 85 | 46.4: Fabrication of InGaIn/GaN-based nano-LEDs for display applications. <i>Digest of Technical Papers SID International Symposium</i> , 2021 , 52, 568-568 | 0.5 | |
| 84 | VT Shift and Recovery Mechanisms of p-GaN Gate HEMTs Under DC/AC Gate Stress Investigated by Fast Sweeping Characterization. <i>IEEE Electron Device Letters</i> , 2021 , 42, 1508-1511 | 4.4 | 8 |
| 83 | Demonstration of Avalanche and Surge Current Robustness in GaN Junction Barrier Schottky Diode With 600-V/10-A Switching Capability. <i>IEEE Transactions on Power Electronics</i> , 2021 , 36, 12163-12167 | 7.2 | 6 |
| 82 | Direct observation of reach-through behavior in back-illuminated algan avalanche photodiode with separate absorption and multiplication structure. <i>Journal Physics D: Applied Physics</i> , 2020 , 53, 425101 | 3 | 2 |
| 81 | Synthesis and Properties of InGaIn/GaN Multiple Quantum Well Nanowires on Si (111) by Molecular Beam Epitaxy. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2020 , 217, 2070028 | 1.6 | |
| 80 | AlGaIn Promising Candidate for High-Electron-Mobility Transistors. <i>IEEE Electron Device Letters</i> , 2020 , 1-1 | 4.4 | 4 |
| 79 | High-Performance 4H-SiC Schottky Photodiode With Semitransparent Grid-Electrode for EUV Detection. <i>IEEE Photonics Technology Letters</i> , 2020 , 32, 791-794 | 2.2 | 4 |
| 78 | After-Pulse Characterizations of Geiger-Mode 4H-SiC Avalanche Photodiodes. <i>IEEE Photonics Technology Letters</i> , 2020 , 32, 706-709 | 2.2 | 1 |
| 77 | Realization of regular resonance mode in GaN-based polygonal microdisks on Si. <i>Journal of Applied Physics</i> , 2020 , 127, 113102 | 2.5 | 0 |
| 76 | High-Responsivity Graphene/4H-SiC Ultraviolet Photodetector Based on a Planar Junction Formed by the Dual Modulation of Electric and Light Fields. <i>Advanced Optical Materials</i> , 2020 , 8, 2000559 | 8.1 | 8 |
| 75 | Do all screw dislocations cause leakage in GaN-based devices?. <i>Applied Physics Letters</i> , 2020 , 116, 062104 | 3.4 | 19 |
| 74 | Highly Enhanced Inductive Current Sustaining Capability and Avalanche Ruggedness in GaN p-i-n Diodes With Shallow Bevel Termination. <i>IEEE Electron Device Letters</i> , 2020 , 41, 469-472 | 4.4 | 7 |
| 73 | 1.4-kV Quasi-Vertical GaN Schottky Barrier Diode With Reverse p-n Junction Termination. <i>IEEE Journal of the Electron Devices Society</i> , 2020 , 1-1 | 2.3 | 6 |
| 72 | Hybrid Light Emitters and UV Solar-Blind Avalanche Photodiodes based on III-Nitride Semiconductors. <i>Advanced Materials</i> , 2020 , 32, e1904354 | 24 | 11 |

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|----|--|-----|----|
| 71 | Multi-aperture anode based AlGaIn/GaN Schottky barrier diodes with low turn-on voltage and high uniformity. <i>Applied Physics Express</i> , 2020 , 13, 096502 | 2.4 | 2 |
| 70 | Synthesis and Properties of InGaIn/GaN Multiple Quantum Well Nanowires on Si (111) by Molecular Beam Epitaxy. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2020 , 217, 1900729 | 1.6 | 3 |
| 69 | Electronic properties of arsenene nanoribbons for FET application. <i>Optical and Quantum Electronics</i> , 2020 , 52, 1 | 2.4 | 0 |
| 68 | High- κ HfO ₂ -Based AlGaIn/GaN MIS-HEMTs With Y ₂ O ₃ Interfacial Layer for High Gate Controllability and Interface Quality. <i>IEEE Journal of the Electron Devices Society</i> , 2020 , 8, 15-19 | 2.3 | 7 |
| 67 | Electron-Beam-Driven III-Nitride Plasmonic Nanolasers in the Deep-UV and Visible Region. <i>Small</i> , 2020 , 16, e1906205 | 11 | 9 |
| 66 | Different I _V Behaviors and Leakage Current Mechanisms in AlGaIn Solar-Blind Ultraviolet Avalanche Photodiodes. <i>ACS Applied Electronic Materials</i> , 2020 , 2, 2716-2720 | 4 | 1 |
| 65 | Nanoplasmonically Enhanced High-Performance Metastable Phase HgGaO Solar-Blind Photodetectors. <i>ACS Applied Materials & Interfaces</i> , 2019 , 11, 40283-40289 | 9.5 | 21 |
| 64 | Gate Reliability of p-GaN Gate AlGaIn/GaN High Electron Mobility Transistors. <i>IEEE Electron Device Letters</i> , 2019 , 40, 379-382 | 4.4 | 16 |
| 63 | Performance Modulation for Back-Illuminated AlGaIn Ultraviolet Avalanche Photodiodes Based on Multiplication Scaling. <i>IEEE Photonics Journal</i> , 2019 , 11, 1-7 | 1.8 | 4 |
| 62 | Performance of Monolayer Blue Phosphorene Double-Gate MOSFETs from the First Principles. <i>ACS Applied Materials & Interfaces</i> , 2019 , 11, 20956-20964 | 9.5 | 22 |
| 61 | Investigation on the Activation Energy of Device Degradation and Switching Time in AlGaIn/GaN HEMTs for High-Frequency Application. <i>IEEE Journal of the Electron Devices Society</i> , 2019 , 1-1 | 2.3 | 0 |
| 60 | Spatial Non-Uniform Hot Carrier Luminescence From 4H-SiC p-i-n Avalanche Photodiodes. <i>IEEE Photonics Technology Letters</i> , 2019 , 31, 447-450 | 2.2 | 6 |
| 59 | A High-Performance SiO ₂ /SiN _x 1-D Photonic Crystal UV Filter Used for Solar-Blind Photodetectors. <i>IEEE Photonics Journal</i> , 2019 , 11, 1-7 | 1.8 | 2 |
| 58 | Precise Extraction of Dynamic R _{dson} Under High Frequency and High Voltage by a Double-Diode-Isolation Method. <i>IEEE Journal of the Electron Devices Society</i> , 2019 , 1-1 | 2.3 | 5 |
| 57 | Janus Ga ₂ SeTe: A Promising Candidate for Highly Efficient Solar Cells. <i>Solar Rrl</i> , 2019 , 3, 1900321 | 7.1 | 5 |
| 56 | Effect of Very High-Fluence Proton Radiation on 6H-SiC Photoconductive Proton Detectors. <i>IEEE Electron Device Letters</i> , 2019 , 40, 1929-1932 | 4.4 | 6 |
| 55 | Magnesium ion-implantation-based gallium nitride p-i-n photodiode for visible-blind ultraviolet detection. <i>Photonics Research</i> , 2019 , 7, B48 | 6 | 20 |
| 54 | Observation and Modeling of Leakage Current in AlGaIn Ultraviolet Light Emitting Diodes. <i>IEEE Photonics Technology Letters</i> , 2019 , 31, 1697-1700 | 2.2 | 2 |

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|----|---|------|----|
| 53 | Effects of dissipative substrate on the performances of enhancement mode AlInN/GaN HEMTs. <i>International Journal of Numerical Modelling: Electronic Networks, Devices and Fields</i> , 2019 , 32, e2482 | 1 | 3 |
| 52 | Vertical 4H-SiC n-i-p-n APDs With Partial Trench Isolation. <i>IEEE Photonics Technology Letters</i> , 2018 , 30, 805-808 | 2.2 | 6 |
| 51 | A Reusable and High Sensitivity Nitrogen Dioxide Sensor Based on Monolayer SnSe. <i>IEEE Electron Device Letters</i> , 2018 , 39, 599-602 | 4.4 | 27 |
| 50 | Improvement of Power Performance of GaN HEMT by Using Quaternary InAlGa _{0.5} N Barrier. <i>IEEE Journal of the Electron Devices Society</i> , 2018 , 6, 360-364 | 2.3 | 16 |
| 49 | High Sensitive pH Sensor Based on AlInN/GaN Heterostructure Transistor. <i>Sensors</i> , 2018 , 18, | 3.8 | 11 |
| 48 | Effective suppression of the high temperature DC performance degradation of AlInN/GaN HEMTs by back barrier. <i>International Journal of Numerical Modelling: Electronic Networks, Devices and Fields</i> , 2018 , 31, e2299 | 1 | 1 |
| 47 | Effects of the Trap Level in the Unintentionally Doped GaN Buffer Layer on Optimized p-GaN Gate AlGa _{0.5} N/GaN HEMTs. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2018 , 215, 1700368 | 1.6 | 4 |
| 46 | Avalanche Ruggedness of GaN p-i-n Diodes Grown on Sapphire Substrate. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2018 , 215, 1800069 | 1.6 | 6 |
| 45 | Temperature Dependence of the Energy Band Diagram of AlGa _{0.5} N/GaN Heterostructure. <i>Advances in Condensed Matter Physics</i> , 2018 , 2018, 1-4 | 1 | 2 |
| 44 | Fine Control of the Electric Field Distribution in the Heterostructure Multiplication Region of AlGa _{0.5} N Avalanche Photodiodes. <i>IEEE Photonics Journal</i> , 2017 , 9, 1-7 | 1.8 | 4 |
| 43 | 4H-SiC Ultraviolet Avalanche Photodiodes With Small Gain Slope and Enhanced Fill Factor. <i>IEEE Photonics Journal</i> , 2017 , 9, 1-8 | 1.8 | 7 |
| 42 | An Improved Design for Solar-Blind AlGa _{0.5} N Avalanche Photodiodes. <i>IEEE Photonics Journal</i> , 2017 , 9, 1-7 | 1.8 | 10 |
| 41 | Manipulable and Hybridized, Ultralow-Threshold Lasing in a Plasmonic Laser Using Elliptical InGa _{0.5} N/GaN Nanorods. <i>Advanced Functional Materials</i> , 2017 , 27, 1703198 | 15.6 | 19 |
| 40 | Photoluminescence Study of the Photoinduced Phase Separation in Mixed-Halide Hybrid Perovskite CH ₃ NH ₃ Pb(Br)I Crystals Synthesized via a Solvothermal Method. <i>Scientific Reports</i> , 2017 , 7, 17695 | 4.9 | 13 |
| 39 | Single Photon Counting Spatial Uniformity of 4H-SiC APD Characterized by SNOM-Based Mapping System. <i>IEEE Photonics Technology Letters</i> , 2017 , 29, 1603-1606 | 2.2 | 7 |
| 38 | 4H-SiC Avalanche Photodiode Linear Array Operating in Geiger Mode. <i>IEEE Photonics Journal</i> , 2017 , 9, 1-7 | 1.8 | 7 |
| 37 | Analysis of Dark Count Mechanisms of 4H-SiC Ultraviolet Avalanche Photodiodes Working in Geiger Mode. <i>IEEE Transactions on Electron Devices</i> , 2017 , 64, 4532-4539 | 2.9 | 11 |
| 36 | 4H-SiC SACM Avalanche Photodiode With Low Breakdown Voltage and High UV Detection Efficiency. <i>IEEE Photonics Journal</i> , 2016 , 8, 1-7 | 1.8 | 12 |

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|----|--|------|----|
| 35 | High Fill-Factor 4H-SiC Avalanche Photodiodes With Partial Trench Isolation. <i>IEEE Photonics Technology Letters</i> , 2016 , 28, 2526-2528 | 2.2 | 16 |
| 34 | High-Performance 4H-SiC p-i-n Ultraviolet Photodiode With p Layer Formed by Al Implantation. <i>IEEE Photonics Technology Letters</i> , 2016 , 28, 1189-1192 | 2.2 | 11 |
| 33 | Light-Emitting Diodes: High Color Rendering Index Hybrid III-Nitride/Nanocrystals White Light-Emitting Diodes (Adv. Funct. Mater. 1/2016). <i>Advanced Functional Materials</i> , 2016 , 26, 156-156 | 15.6 | |
| 32 | Significant improvements in InGaN/GaN nano-photoelectrodes for hydrogen generation by structure and polarization optimization. <i>Scientific Reports</i> , 2016 , 6, 20218 | 4.9 | 24 |
| 31 | A method of applying compressive pre-stress to AlGaIn barrier in AlGaIn/GaN heterostructures by depositing an additional thermally mismatched dielectric. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2016 , 213, 2474-2478 | 1.6 | 1 |
| 30 | Enhanced InGaIn/GaN photoelectrodes for visible-light-driven hydrogen generation by surface roughening. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2016 , 213, 2704-2708 | 1.6 | 1 |
| 29 | Improved Schottky contacts to InGaIn alloys by a photoelectrochemical treatment. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2016 , 213, 1034-1038 | 1.6 | |
| 28 | High-voltage photoconductive semiconductor switches fabricated on semi-insulating HVPE GaN:Fe template. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2016 , 13, 374-377 | | 4 |
| 27 | High-Quality Crystal Growth and Characteristics of AlGaIn-Based Solar-Blind Distributed Bragg Reflectors with a Tri-layer Period Structure. <i>Scientific Reports</i> , 2016 , 6, 29571 | 4.9 | 6 |
| 26 | Highly selective and sensitive phosphate anion sensors based on AlGaIn/GaN high electron mobility transistors functionalized by ion imprinted polymer. <i>Scientific Reports</i> , 2016 , 6, 27728 | 4.9 | 33 |
| 25 | High Color Rendering Index Hybrid III-Nitride/Nanocrystals White Light-Emitting Diodes. <i>Advanced Functional Materials</i> , 2016 , 26, 36-43 | 15.6 | 41 |
| 24 | High-temperature and reliability performance of 4H-SiC Schottky-barrier photodiodes for UV detection. <i>Journal of Vacuum Science and Technology B: Nanotechnology and Microelectronics</i> , 2015 , 33, 040602 | 1.3 | 9 |
| 23 | Utilization of FIB Technique in TEM Specimen Preparation of GaN-based Devices for Dislocation Investigation. <i>Microscopy and Microanalysis</i> , 2015 , 21, 1991-1992 | 0.5 | |
| 22 | Determination of Temperature-Dependent Stress State in Thin AlGaIn Layer of AlGaIn/GaN HEMT Heterostructures by Near-Resonant Raman Scattering. <i>Advances in Condensed Matter Physics</i> , 2015 , 1-6 | 1 | |
| 21 | Demonstration of an AlGaIn-based solar-blind high-voltage photoconductive switch. <i>Journal of Vacuum Science and Technology B: Nanotechnology and Microelectronics</i> , 2015 , 33, 040601 | 1.3 | 6 |
| 20 | High-Temperature Single Photon Detection Performance of 4H-SiC Avalanche Photodiodes. <i>IEEE Photonics Technology Letters</i> , 2014 , 26, 1136-1138 | 2.2 | 44 |
| 19 | Reverse leakage current in AlGaIn-based ultraviolet light-emitting diodes. <i>Science Bulletin</i> , 2014 , 59, 1276-1279 | | 5 |
| 18 | Significant Performance Improvement in AlGaIn Solar-Blind Avalanche Photodiodes by Exploiting the Built-In Polarization Electric Field. <i>IEEE Journal of Selected Topics in Quantum Electronics</i> , 2014 , 20, 187-192 | 3.8 | 23 |

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|----|---|------|----|
| 17 | Spatially localised luminescence emission properties induced by formation of ring-shaped quasi-potential trap around V-pits in InGaN epi-layers. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2014 , 211, 2823-2827 | 1.6 | 9 |
| 16 | Large-Swing a-IGZO Inverter With a Depletion Load Induced by Laser Annealing. <i>IEEE Electron Device Letters</i> , 2014 , 35, 1034-1036 | 4.4 | 24 |
| 15 | Enhanced bias stress stability of a-InGaZnO thin film transistors by inserting an ultra-thin interfacial InGaZnO:N layer. <i>Applied Physics Letters</i> , 2013 , 102, 193505 | 3.4 | 50 |
| 14 | High Quantum Efficiency GaN-Based p-i-n Ultraviolet Photodetectors Prepared on Patterned Sapphire Substrates. <i>IEEE Photonics Technology Letters</i> , 2013 , 25, 652-654 | 2.2 | 32 |
| 13 | Improvements in Microstructure and Leakage Current of High-In-Content InGaN p-i-n Structure by Annealing. <i>IEEE Photonics Technology Letters</i> , 2012 , 24, 1478-1480 | 2.2 | 3 |
| 12 | Ultra-Low Dark Current AlGaIn-Based Solar-Blind Metal Semiconductor Metal Photodetectors for High-Temperature Applications. <i>IEEE Sensors Journal</i> , 2012 , 12, 2086-2090 | 4 | 57 |
| 11 | Bias-Selective Dual-Operation-Mode Ultraviolet Schottky-Barrier Photodetectors Fabricated on High-Resistivity Homoepitaxial GaN. <i>IEEE Photonics Technology Letters</i> , 2012 , 24, 2203-2205 | 2.2 | 7 |
| 10 | Characteristics of polarization-doped N-face III-nitride light-emitting diodes. <i>Applied Physics Letters</i> , 2012 , 100, 073507 | 3.4 | 12 |
| 9 | GaN MSM photodetectors fabricated on bulk GaN with low dark-current and high UV/visible rejection ratio. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2011 , 8, 2473-2475 | | 9 |
| 8 | Field-dependent carrier trapping induced kink effect in AlGaIn/GaN high electron mobility transistors. <i>Applied Physics Letters</i> , 2011 , 98, 173508 | 3.4 | 29 |
| 7 | Forward tunneling current in GaN-based blue light-emitting diodes. <i>Applied Physics Letters</i> , 2010 , 96, 083504 | 3.4 | 68 |
| 6 | On the reverse gate leakage current of AlGaIn/GaN high electron mobility transistors. <i>Applied Physics Letters</i> , 2010 , 97, 153503 | 3.4 | 92 |
| 5 | Growth of In-rich and Ga-rich InGaN alloys by MOCVD and fabrication of InGaN-based photoelectrodes. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2010 , 7, 1817-1820 | | 14 |
| 4 | Efficiency droop behavior of direct current aged GaN-based blue light-emitting diodes. <i>Applied Physics Letters</i> , 2009 , 95, 163504 | 3.4 | 19 |
| 3 | InGaIn/GaN multi-quantum-well-based light-emitting and photodetective dual-functional devices. <i>Frontiers of Optoelectronics in China</i> , 2009 , 2, 442-445 | | 0 |
| 2 | Stable response to visible light of InGaN photoelectrodes. <i>Applied Physics Letters</i> , 2008 , 92, 262110 | 3.4 | 50 |
| 1 | Achieving Record High External Quantum Efficiency >86.7% in Solar-Blind Photoelectrochemical Photodetection. <i>Advanced Functional Materials</i> , 2016 , 26, 1601604 | 15.6 | 4 |